

AMENDMENTS TO THE SPECIFICATION

Please amend the Specification pursuant to 37 C.F.R. § 1.121 as follows:

Please amend the text at page 3, line 16, bridging page 4, line 3, as follows:

According to another aspect of the present invention, there is also provided a method for growing a nitride semiconductor epitaxial layer, including a first step of growing a first nitride semiconductor epitaxial layer containing indium at a first temperature, a second step of growing a second nitride semiconductor epitaxial layer whose equilibrium vapor pressure of nitrogen is higher lower than that of the first nitride semiconductor epitaxial layer, on the first nitride semiconductor epitaxial layer at a second temperature, and a third step of releasing nitrogen from the first nitride semiconductor epitaxial layer by increasing a temperature to a third temperature higher than the second temperature to convert the first nitride semiconductor epitaxial layer into a metal layer.